



《风光欣》技术资料

C2328

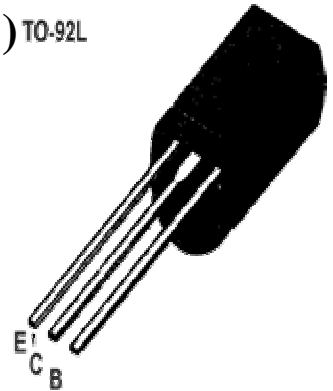
NPN EPITAXIAL SILICON TRANSISTOR

AUDIO POWER AMPLIFIER APPLICATIONS

- *Complement to A928
- *Collector Dissipation PC=1W
- *3 Watt Output Application

ABSOLUTE MAXIMUM RATINGS(TA=25) TO-92L

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	30	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter -Base Voltage	V _{EBO}	5	V
Collector Current	I _c	2	A
Collector Dissipation	P _c	1	W
Junction Temperature	T _j	150	
Storage Temperature	T _{STG}	-55 ~ +150	



ELECTRICAL CHARACTERISTICS(TA=25)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV _{CB0}	I _c = 100μA, I _E =0	30			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _c = 10mA, I _B =0	30			V
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E = 1mA, I _c =0	5			V
Collector Cut-off Current	I _{CBO}	V _{CB} = 30V, I _E =0			100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 5V, I _c =0,			100	nA
DC Current Gain	h _{FE}	V _{CE} = 2V, I _c =500mA,	100		320	
Base-Emitter On Voltage	V _{BE(on)}	V _{CE} = 2V, I _c = 500mA			1.0	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c = 1.5A, I _B =0.03A			2.0	V
Current Gain -Bandwidth product	f _T	V _{CE} = 2V, I _c = 500mA		120		MHZ
Output Capacitance	C _{OB}	V _{CB} = 10V, I _E = 0, f=1MHZ		30		pF

Hfe CLASSIFICATION

Classification	O	Y
HFE	100~200	160~320